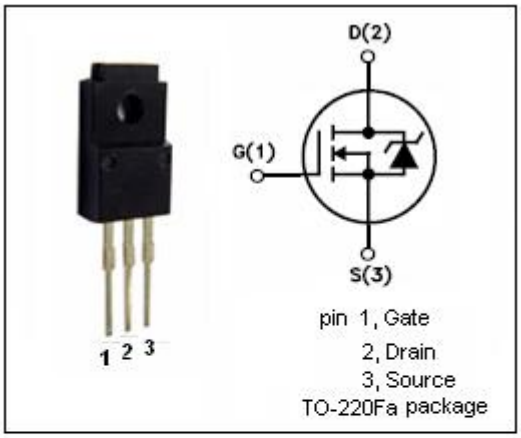
isc N-Channel MOSFET Transistor 2SK755

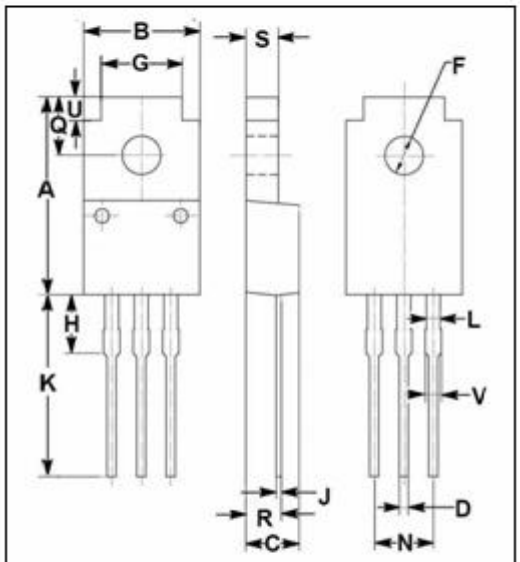


DESCRIPTION

- Drain Current –I_D=5A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=200V(Min)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- high speed power switching



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	200	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	5	A
P_{tot}	Total Dissipation@TC=25℃	40	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.0	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=10 V_{GS}; I_D=1mA	1.0		5.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}=10V; I_D= 3A			0.5	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±16V;V_{DS}= 0			±10	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=160V; V_{GS}= 0			250	uA
V_{SD}	Diode Forward Voltage	I_F=5A; V_{GS}=0		1.0		V